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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/531,603	04/14/2005	Paulus Petrus Franciscus Maria Bruin	NL 021020	8229
65913	7590	01/16/2008		
NXP, B.V. NXP INTELLECTUAL PROPERTY DEPARTMENT M/S41-SJ 1109 MCKAY DRIVE SAN JOSE, CA 95131			EXAMINER ALMO, KHAREEM E	
			ART UNIT 2816	PAPER NUMBER
			NOTIFICATION DATE 01/16/2008	DELIVERY MODE ELECTRONIC

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Notice of the Office communication was sent electronically on above-indicated "Notification Date" to the following e-mail address(es):

ip.department.us@nxp.com

Office Action Summary

Application No.

10/531,603

Applicant(s)

BRUIN ET AL.

Examiner

Khareem E. Almo

Art Unit

2816

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 17 September 2007.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-6 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 1-5 is/are rejected.
- 7) ☒ Claim(s) 6 is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☒ The drawing(s) filed on 15 April 2005 is/are: a) ☒ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☒ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☒ All b) ☐ Some * c) ☐ None of:
1. ☒ Certified copies of the priority documents have been received.
 2. ☐ Certified copies of the priority documents have been received in Application No. _____.
 3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- | | |
|--|---|
| 1) <input checked="" type="checkbox"/> Notice of References Cited (PTO-892) | 4) <input type="checkbox"/> Interview Summary (PTO-413) |
| 2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948) | Paper No(s)/Mail Date. _____ |
| 3) <input type="checkbox"/> Information Disclosure Statement(s) (PTO/SB/08) | 5) <input type="checkbox"/> Notice of Informal Patent Application |
| Paper No(s)/Mail Date. _____ | 6) <input type="checkbox"/> Other: _____ |

DETAILED ACTION

Claim Rejections - 35 USC § 103

1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

2. Claims 1-5 rejected under 35 U.S.C. 103(a) as being unpatentable over Van Der Zee (US 6100750) in view of Itou et al. (US 5594279).

With respect to claim 1, figures 2, 5, 6 and 7 of Van Der Zee disclose a voltage divider arrangement comprising a reference terminal (going into 1), an input terminal (going into 2) for receiving an input signal with respect to said reference terminal (going into 1), an output terminal (3) for supplying an output signal with respect to said reference terminal (going into 1), and a resistor arrangement (R1-RM+1) arranged on a substrate (SBSTR) and coupled between said input terminal (going into 2) and said reference terminal (going into 1), wherein said distributed compensation capacitance structure is separated from said resistor arrangement (R1-RM+1) and said substrate (SBSTR) by respective insulation layers but fails to disclose wherein a distributed compensation capacitance structure for compensating the influence of a distributed parasitic capacitance is arranged between said resistor arrangement (R1-RM+1) and said substrate (SBSTR). Figure 7b of Itou et al. teaches using shielding between power source and substrate to suppress variation. It would be obvious to one skilled in the art

to use the wiring structure in Itou in the circuit of Van Der Zee for the Itou disclosed reason of suppressing variation in the potential and therefore reducing noise.

With respect to claim 2, the above combination discloses a voltage divider arrangement according to claim 1, wherein said resistor arrangement has a meandering shape.

With respect to claim 3, the above combination discloses a voltage divider arrangement according to claim 2, wherein said resistor arrangement is made of polysilicon (see column 4 lines 5-10 of Van Der Zee).

With respect to claim 4, the above combination discloses a voltage divider arrangement according to claim 1, wherein said distributed compensation capacitance structure (4) comprises a conductor layer of a predetermined shape.

With respect to claim 5, the above combination (in figures 6 and 7 of Van Der Zee) disclose a voltage divider arrangement according to claim 4, wherein said predetermined shape is a triangular shape.

3. Claims 1-5 rejected under 35 U.S.C. 103(a) as being unpatentable over Van Der Zee (US 6100750) in view of Hopper (6414367)

With respect to claim 1, figures 2, 5, 6 and 7 of Van Der Zee disclose a voltage divider arrangement comprising a reference terminal (going into 1), an input terminal (going into 2) for receiving an input signal with respect to said reference terminal (going into 1), an output terminal (3) for supplying an output signal with respect to said reference terminal (going into 1), and a resistor arrangement (R1-RM+1) arranged on a

substrate (SBSTR) and coupled between said input terminal (going into 2) and said reference terminal (going into 1), wherein said distributed compensation capacitance structure is separated from said resistor arrangement (R1-RM+1) and said substrate (SBSTR) by respective insulation layers but fails to disclose wherein a distributed compensation capacitance structure for compensating the influence of a distributed parasitic capacitance is arranged between said resistor arrangement (R1-RM+1) and said substrate (SBSTR). Figure 4a of Hopper teaches the use of an insulator (interlayer dielectric 306) to reduce variation in parasitic capacitance between the metal layer and the substrate. It would be obvious at the time the invention was made, to a person of ordinary skill in the art to put the dielectric layer of Hopper between metal layer and substrate of Van Der Zee for the Hopper disclosed purpose of reducing the variation in parasitic capacitance.

With respect to claim 2, the above combination discloses a voltage divider arrangement according to claim 1, wherein said resistor arrangement has a meandering shape.

With respect to claim 3, the above combination discloses a voltage divider arrangement according to claim 2, wherein said resistor arrangement is made of polysilicon (see column 4 lines 5-10 of Van Der Zee).

With respect to claim 4, the above combination discloses a voltage divider arrangement according to claim 1, wherein said distributed compensation capacitance structure (4) comprises a conductor layer of a predetermined shape.

With respect to claim 5, the above combination (in figures 6 and 7 of Van Der

Zee) disclose a voltage divider arrangement according to claim 4, wherein said predetermined shape is a triangular shape.

Allowable Subject Matter

4. Claim 6 objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

With respect to claim 6, the prior art of record fails to suggest or disclose the voltage divider arrangement wherein the width of said conductor layer in the horizontal direction is selected according to the equation $D_k = \frac{DR}{1 + kM + 1 - kCCMP_{sq} CP_{sq}}$, wherein CP_{sq} denotes the parasitic capacitance per unit area of resistor, DR denotes the length of said resistor arrangement (20), k denotes an index of a segment of said transistor arrangement (20); M denotes the total number of segments of said transistor arrangement (20), $CCMP_{sq}$ denotes the distributed compensation capacitance per unit area of resistor and $D_{sub.k}$ denotes said width of said conductor layer.

Response to Arguments

5. Applicant's arguments with respect to claims 1-5 have been considered but are moot in view of the new ground(s) of rejection.

6. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Khareem E. Almo whose telephone number is (571) 272-5524. The examiner can normally be reached on Mon-Fri (8:30-5:00).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Drew Richards can be reached on (571) 272-1736. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.



/QUAN TRA/
PRIMARY EXAMINER
AU 2816
